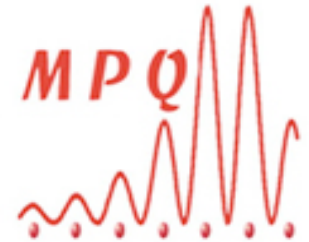


# Current correlations in the self-dual Interacting Resonant Level Model

Edouard Boulat

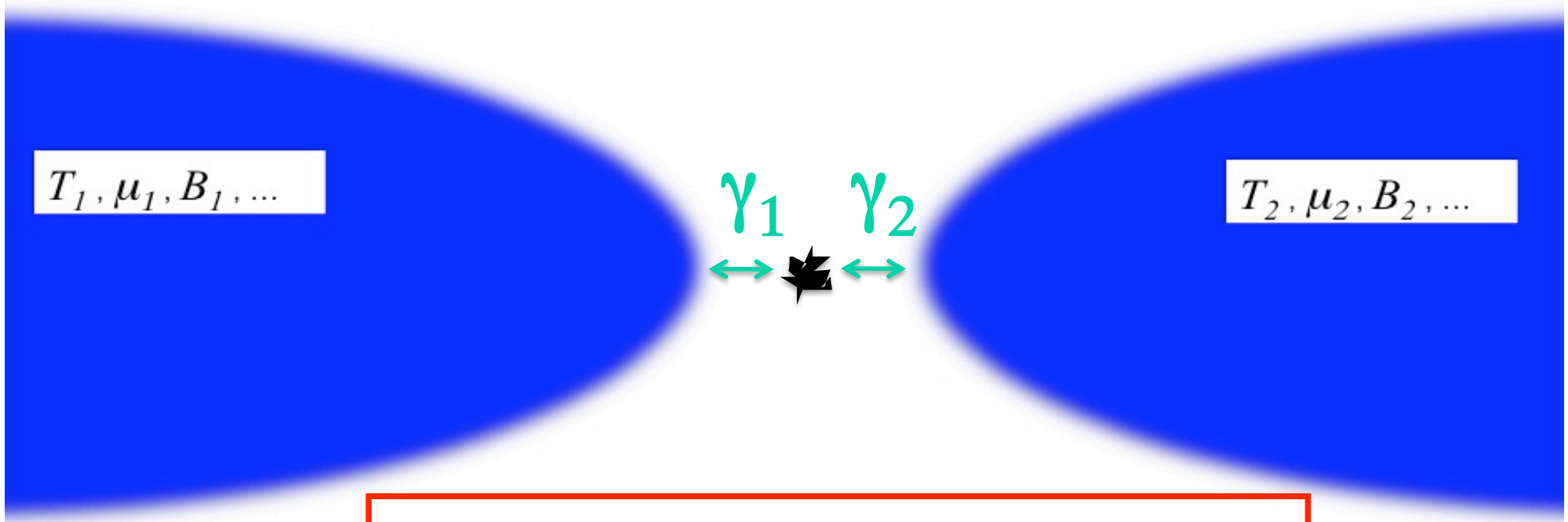
Université Paris 7- Paris Diderot



Collaborators: Alexander Branschädel (TKM, Karlsruhe)  
Peter Schmitteckert (TKM, Karlsruhe)  
Hubert Saleur (CEA Saclay, Paris)

# Impurity out-of-equilibrium

- Several baths (macroscopic, at equilibrium)
- Flow (of charge, spin, energy, ...) through impurity
- Steady state



Questions: current  $I(\mu_1, \mu_2, \dots)$  ?  
fluctuations  $\Delta I(\mu_1, \mu_2, \dots)$  ?  
.....

# Perturbative treatment

➤ Keldysh method:

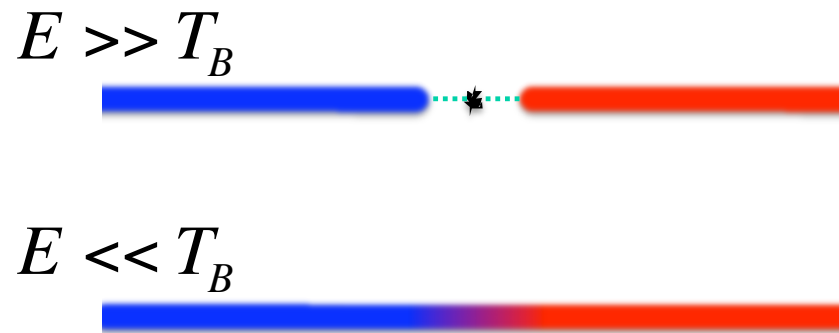
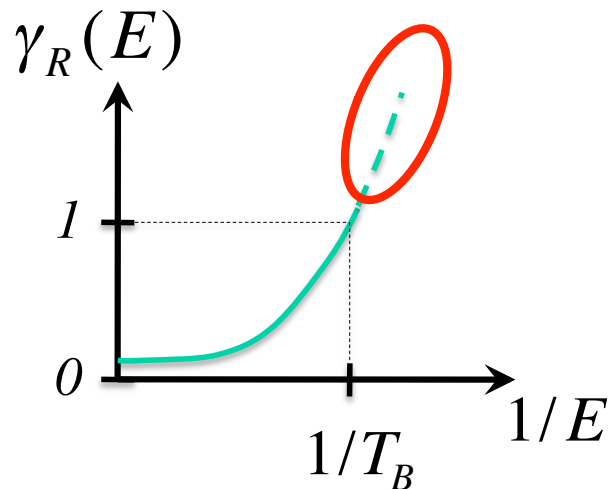
- allows for a formal expression of the out-of-equilibrium density matrix

$$\hat{\rho}(t) = \mathcal{U}(0,t) \hat{\rho}(0) \mathcal{U}(0,t)^{-1}$$

$$\mathcal{U}(0,t) = \mathcal{P} e^{-i \gamma \int_0^t dt' H_I(t')}$$

- but how to evaluate/resum the perturbative expansion?

Crucial in the strong coupling regime



# Perturbative treatment

## ➤ Keldysh method:

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$$\mathcal{U}(0,t) = \mathcal{P} e^{-i \gamma \int_0^t dt' H_I(t')}$$

- but how to evaluate/resum the perturbative expansion?

Crucial in the strong coupling regime

## ➤ How to control approximate methods?

- non-equilibrium RG
- truncated EOM
- etc...



Need for non-perturbative methods

# Non-perturbative approaches

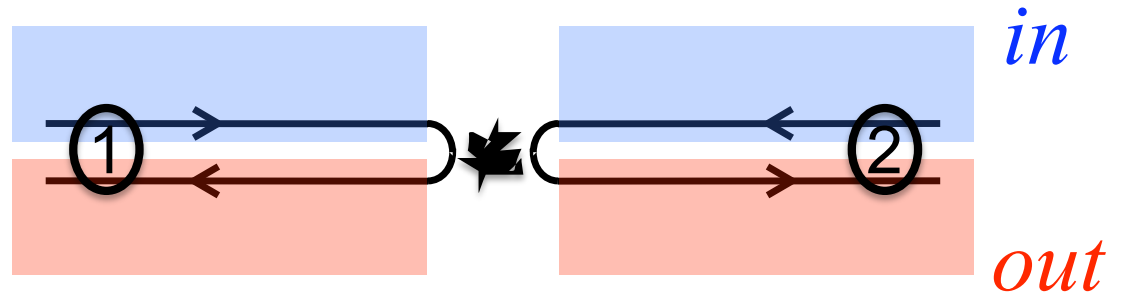
- ➔ • Dressed TBA (Quantum Hall edge states tunneling)  
(P.Fendley, A.W.W.Ludwig, H.Saleur 1995)
- Map to equilibrium problem (boundary sine Gordon model)  
(V.Bazhanov, S.Lukyanov, A.B.Zamolodchikov 1999)
- Effectively non-interacting systems (free fermions)
  - 1-ch Kondo (A. Schiller, U. Hershfield 1998)
  - Luttinger L. (A. Komnik, O. Gogolin 2003)
  - 2-ch Kondo (E. Sela, I. Affleck 2009)    QCP & vicinity } Toulouse point
- Scattering Bethe Ansatz (IRLM)  
(P.Mehta, N.Andrei 2006)

# Outline

- Scattering approach (“dressed TBA”)
  - Why ?
  - When ?
- Interacting Resonant Level Model:
  - Self dual point
  - Current & Noise
- Time dependent DMRG

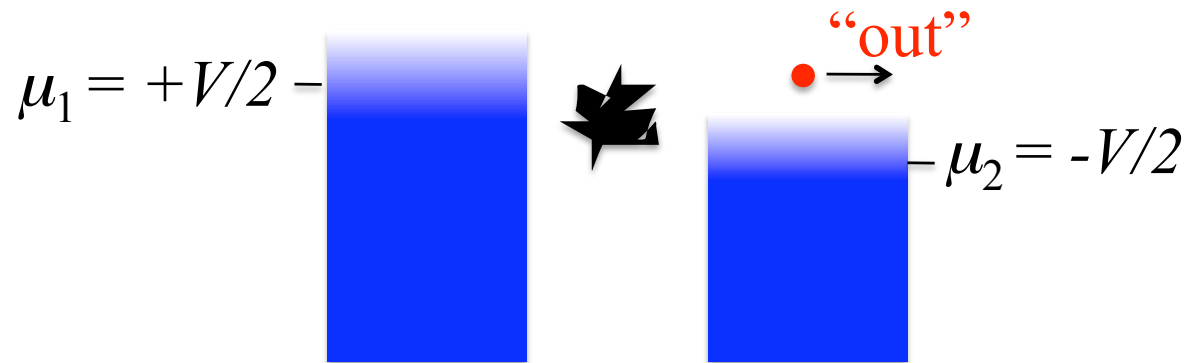
# Modeling the electrodes

- Mapping to 1D
  - linearization around  $k_F$
  - « *in* » and « *out* » modes



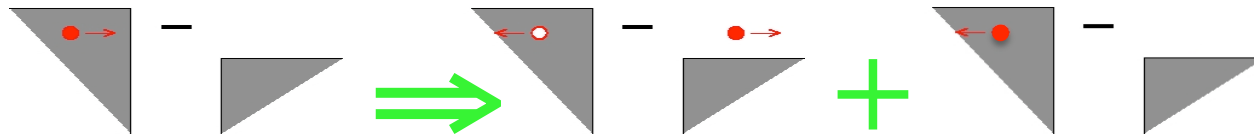
- What is a bath ?

- A reservoir of **incoming** electrons with definite:
  - temperature
  - chemical potentials  $\mu_1, \mu_2$
- Outcoming electrons:
  - They are **not** thermalized right after the impurity.
  - Hypothesis (« **good baths** ») : their (non-equilibrium) distribution don't affect incoming electrons.



# No interactions

- Incoming particle can be either transmitted or reflected



- Generalizes to N-particle states (factorization)

→ Landauer-Büttiker formula: 
$$I = \int dE (f_1(E) - f_2(E)) T(E)$$

scattering states:

$$|1\rangle = |1\rangle^{in} + R_{11}|1\rangle^{out} + R_{12}|2\rangle^{out}$$

$$|2\rangle = |2\rangle^{in} + R_{21}|1\rangle^{out} + R_{22}|2\rangle^{out}$$

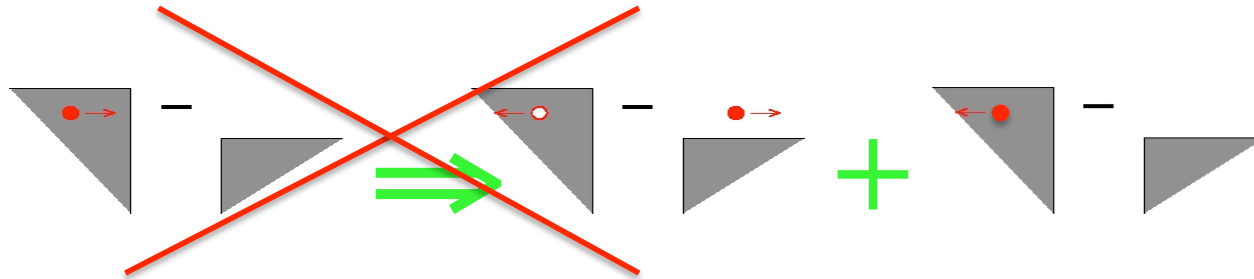
Fermi functions  
for **in-coming electrons**  
in wires (1) and (2)

transmission probability

$$T = |R_{12}|^2$$

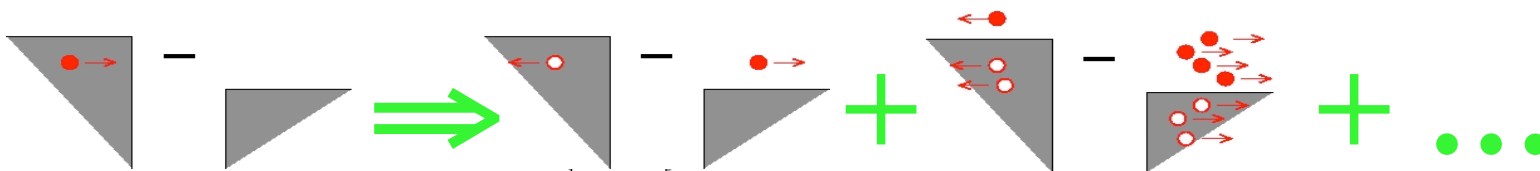


# With interactions



- There is **particle production**
- N-particle state ....

~~$$I = \int dE (f_1(E) - f_2(E)) T(E)$$~~



# Scattering approach

## 1. Build the scattering states:

- N-body electronic states diagonalizing  $H=H_0+H_I$
- Relies on integrability of  $H$  (“**equilibrium property**”)
- **No particle production**
- **Factorization**



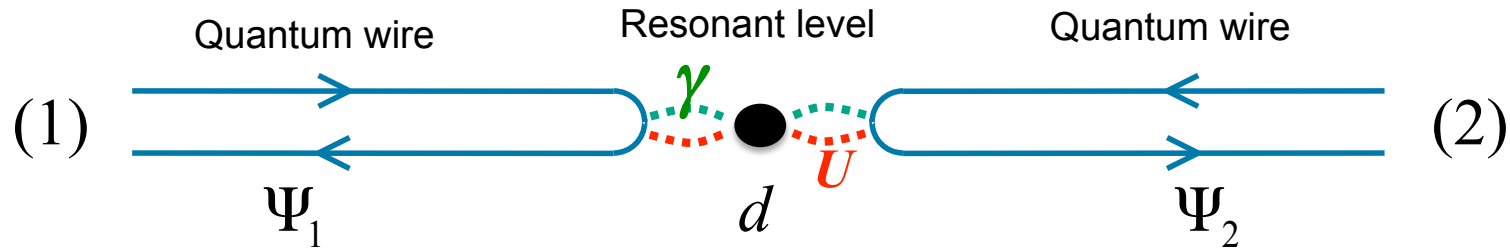
$$||\alpha, p\rangle\rangle = |\alpha, p\rangle^{in} + R_{\alpha\beta}(p) |\beta, p\rangle^{out}$$

## 2. Impose a voltage

- Represent incoming Fermi seas in the basis of scattering states
- Determine the proper distribution for incoming quasiparticles  $\rho_\alpha(p, V)$
- Non-trivial condition !!! (**severe requirement**)

# IRLM

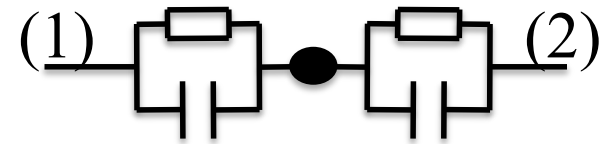
## Interacting Resonant Level Model



Hamiltonian:  $H = H_0 + H_I$

$$H_0 = -iv_F \sum_{a=1,2} \int_{-\infty}^{\infty} dx \Psi_a^\dagger \partial_x \Psi_a(x)$$

electrodes



$$H_I = \left( \gamma_1 \Psi_1^\dagger(0) + \gamma_2 \Psi_2^\dagger(0) \right) d + \text{h.c.} + U \left( : \Psi_1^\dagger \Psi_1 : (0) + : \Psi_2^\dagger \Psi_2 : (0) \right) \left( d^\dagger d - \frac{1}{2} \right) + \varepsilon_d d^\dagger d$$

tunnelling

Coulombic repulsion

Gate voltage  
 $\varepsilon_d = 0$  at resonance

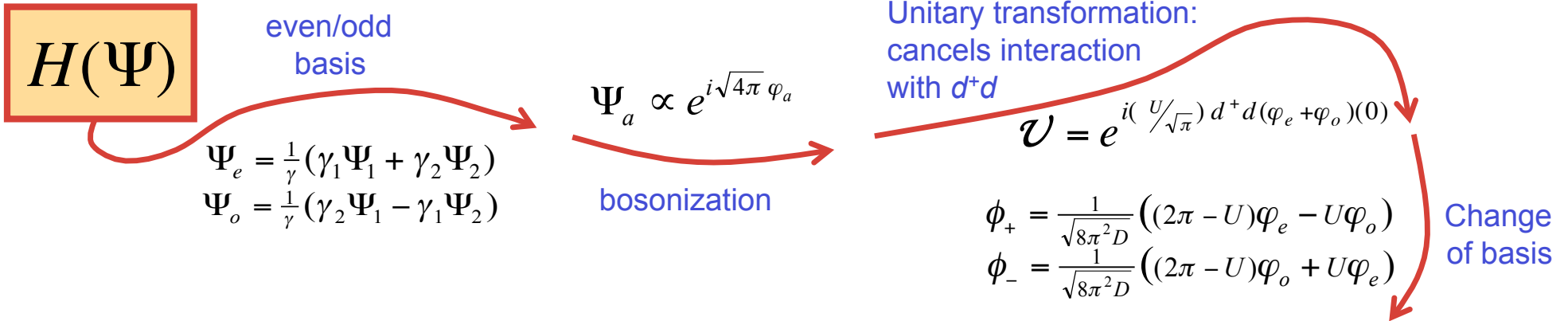
# Route

1. Build the scattering states



2. Impose a voltage  $\leftarrow \rightarrow$  represent biased Fermi seas

# Scattering states



Self dual point  $U=U^*$

→ Scaling dimension  $D(U^*)=1/4$

→ Enhanced SU(2) symmetry in the bulk

$$J^z = \frac{1}{2}(\Psi_e^\dagger\Psi_e - \Psi_o^\dagger\Psi_o) \quad J^+ = \Psi_e^\dagger\Psi_o$$

**anisotropic Kondo model**

$$H = H_0(\phi_+) + H_0(\phi_-) + H_I$$

$$H_I = \gamma e^{i\sqrt{8\pi D}\phi_+(0)}d^+ + \text{h.c.}$$

**Scattering modes  $A_\alpha(p)$**  (sine Gordon  $\beta = \sqrt{2\pi}$ ):

2 solitons  $A_\pm(p)$  charge  $\pm 2$

2 breathers  $A_{0,1}(p)$  charge 0

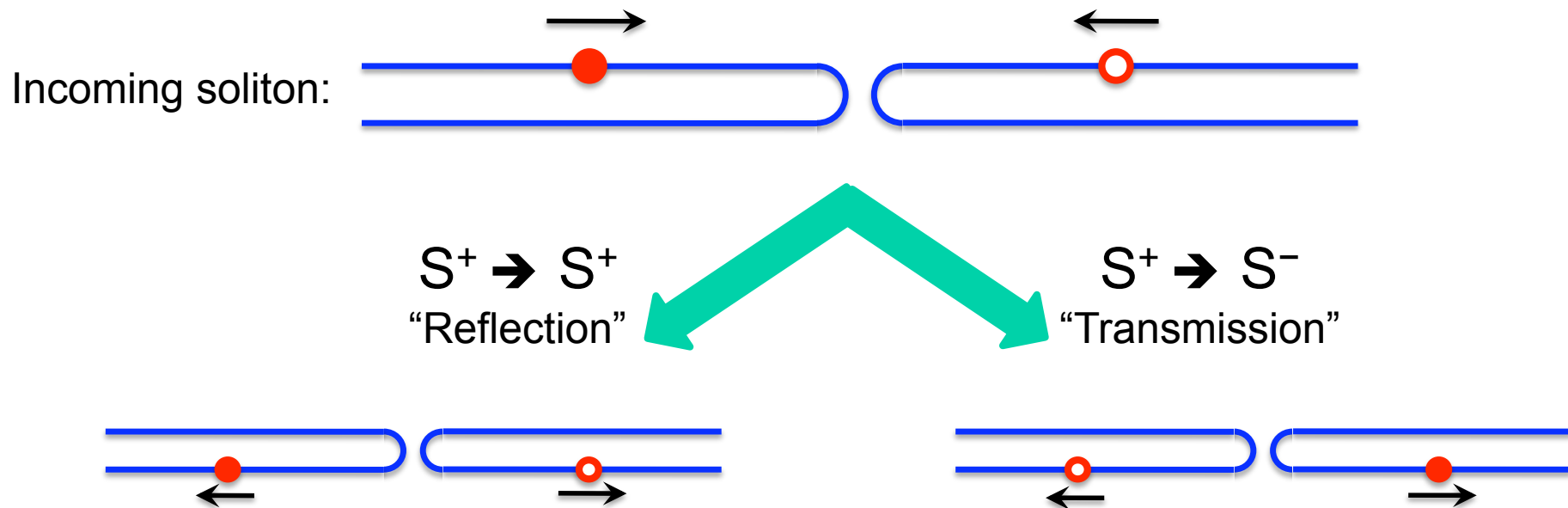
$$R_{\alpha\beta}(p) = \begin{pmatrix} \frac{1}{2}(R_1^K + P^K) & \frac{1}{2}(R_1^K - P^K) & 0 & 0 \\ \frac{1}{2}(R_1^K - P^K) & \frac{1}{2}(R_1^K + P^K) & 0 & 0 \\ 0 & 0 & P^K & 0 \\ 0 & 0 & 0 & R_0^K \end{pmatrix} \begin{matrix} + \\ - \\ 1 \\ 0 \end{matrix}$$

$$P^K = \tanh\left(\ln\sqrt{\frac{p}{T_b}} - \frac{i\pi}{4}\right)$$

$$R_\alpha^K = \frac{\tanh\left(\ln\sqrt{\frac{p}{T_b}} - \frac{i\pi(2-\alpha)}{12}\right)}{\tanh\left(\ln\sqrt{\frac{p}{T_b}} + \frac{i\pi(2-\alpha)}{12}\right)}$$

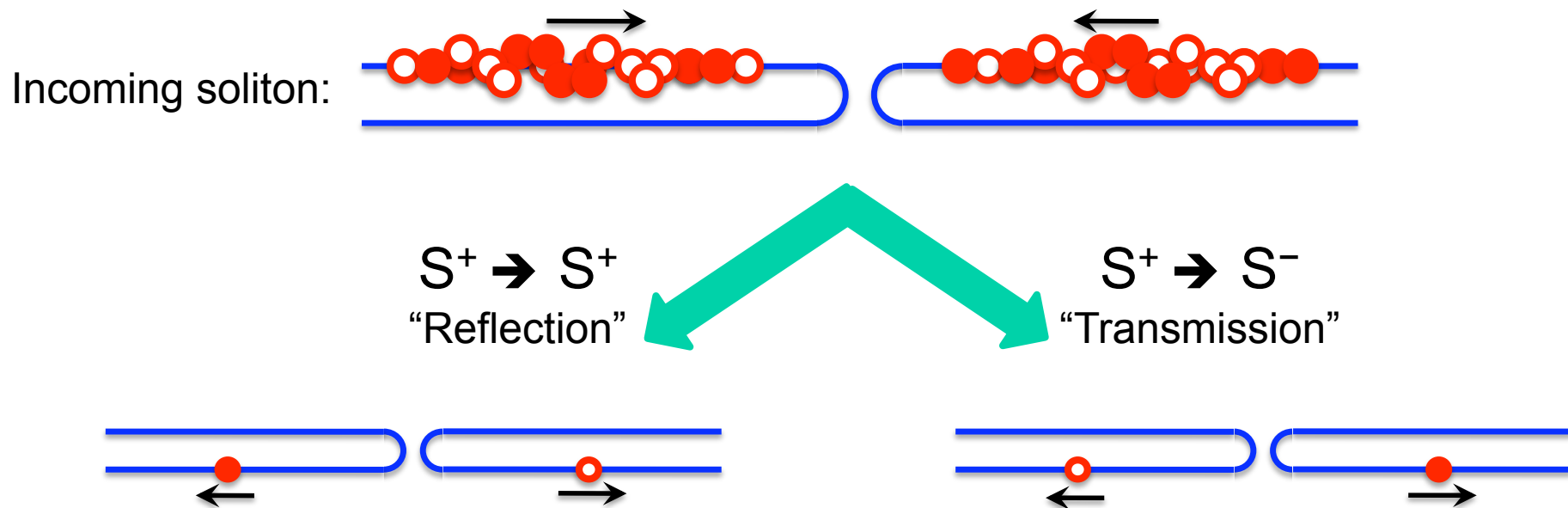
# A caricature of solitons

- Charge carriers: solitons ( $S^+$ ) and antisolitons ( $S^-$ )
- Charges:
  - Globally neutral:  $Q_1 + Q_2 = 0$
  - Relative charge:  $Q_1 - Q_2 = \pm 2e$



# A caricature of solitons

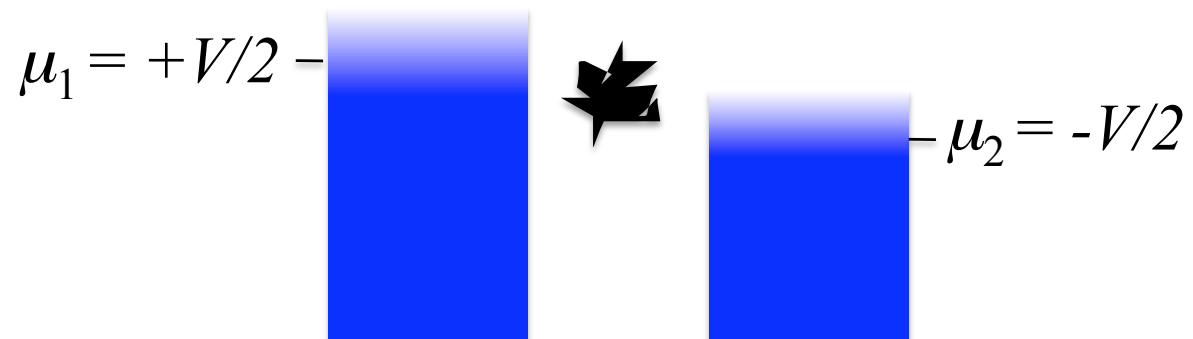
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  - Relative charge:  $Q_1 - Q_2 = \pm 2e$



# Route

1. Build the scattering states

2. Impose a voltage  $\leftrightarrow$  represent biased Fermi seas





# Density matrix

2. Represent **incoming** Fermi seas in the basis of scattering states:

$$\hat{\rho} \propto \exp\left[-\frac{1}{k_B T} (H + Y)\right]$$

Hersfield's operator

Incoming fields: don't feel the impurity

$$Y = \frac{V}{2} \int_{-\infty}^0 dx (\Psi_1^+ \Psi_1 - \Psi_2^+ \Psi_2) = \frac{V}{2} (N_1^{in} - N_2^{in})$$

Represent  $Y$  in the q.p. basis: in general: **particle production !**

**Sufficient** condition to avoid this: it is a one-particle operator:

$$Y \cdot A_{\alpha}^{+,in}(p) = Y_{\alpha\beta}(p) A_{\beta}^{+,in}(p)$$

→ At the self-dual point,  $Y$  is the **charge** : diagonal !

$$Y \cdot A_{\alpha}^{+,in}(p) = \frac{q_{\alpha} V}{2} A_{\alpha}^{+,in}(p) \quad q_{\alpha} = 0, \pm 2$$

# Y operator


- Closed expressions for the  $Y$  operator:

- In terms of the “in” algebra:

$$\hat{Y} = V \mathcal{J}^{z,in} = V \int dp \mathcal{J}^{z,in}(p)$$



$$\mathcal{J}^a(p) = \sum_{\alpha,\beta=0,\pm} A_\alpha^+(p) [J^a]_{\alpha\beta} A_\beta(p)$$

$$\mathcal{J}^z(p) = A_+^+(p)A_+(p) - A_-^+(p)A_-(p)$$

 
$$\langle A_\alpha^{+,in}(p) A_\beta^{in}(p') \rangle = \delta_{\alpha\beta} \delta(p - p') \rho_\alpha(p, V)$$

- In terms of the “out” algebra: **NON DIAGONAL CORRELATIONS!**
- In terms of electrons: **NON LOCAL!**

$$\hat{Y} = V \int dp h^a(p) \mathcal{J}^{a,out}(p)$$

 
$$\langle A_\alpha^{+,out}(p) A_\beta^{out}(p') \rangle = \delta(p - p') R_{\alpha\gamma}^+(p) \rho_\gamma(p, V) R_{\gamma\beta}(p)$$


# Observables

- Current:

$$\hat{I} = Q^{in} - Q^{out} = \int dp \sum_{\alpha} q_{\alpha} (A_{\alpha}^{+,in}(p) A_{\alpha}^{in}(p) - A_{\alpha}^{+,out}(p) A_{\alpha}^{out}(p))$$

→ recover Landauer Buttiker formula:

$$\langle I \rangle = \sum_{\alpha} \int dp \rho_{\alpha}(p) \tau_{\alpha}^{-1}(p)$$

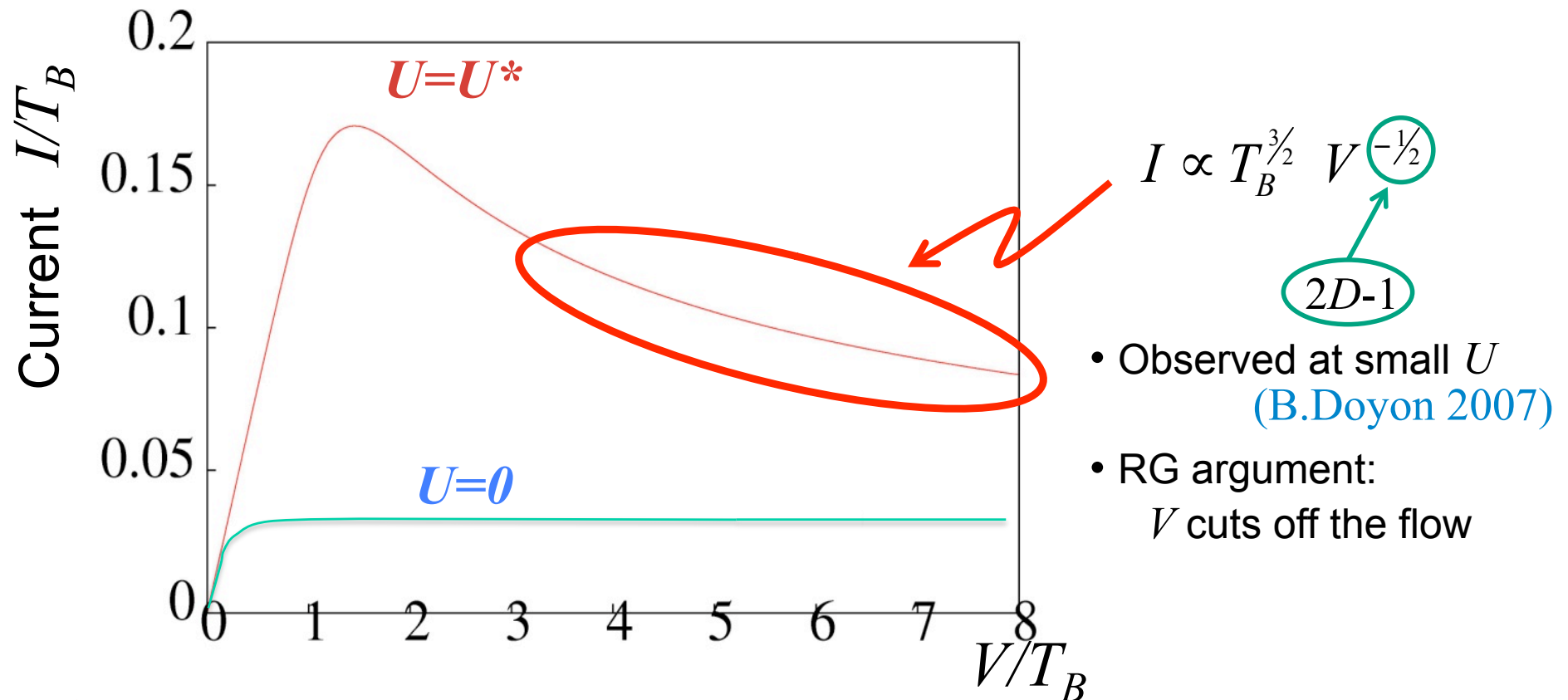
Charge transfer rate

$$\tau_{\alpha}^{-1}(p) = \sum_{\beta} (q_{\alpha} - q_{\beta}) |R_{\alpha\beta}(p)|^2$$

- DC Noise:

$$\hat{S} = \left( \hat{I} - \langle \hat{I} \rangle \right)^2 = \dots$$

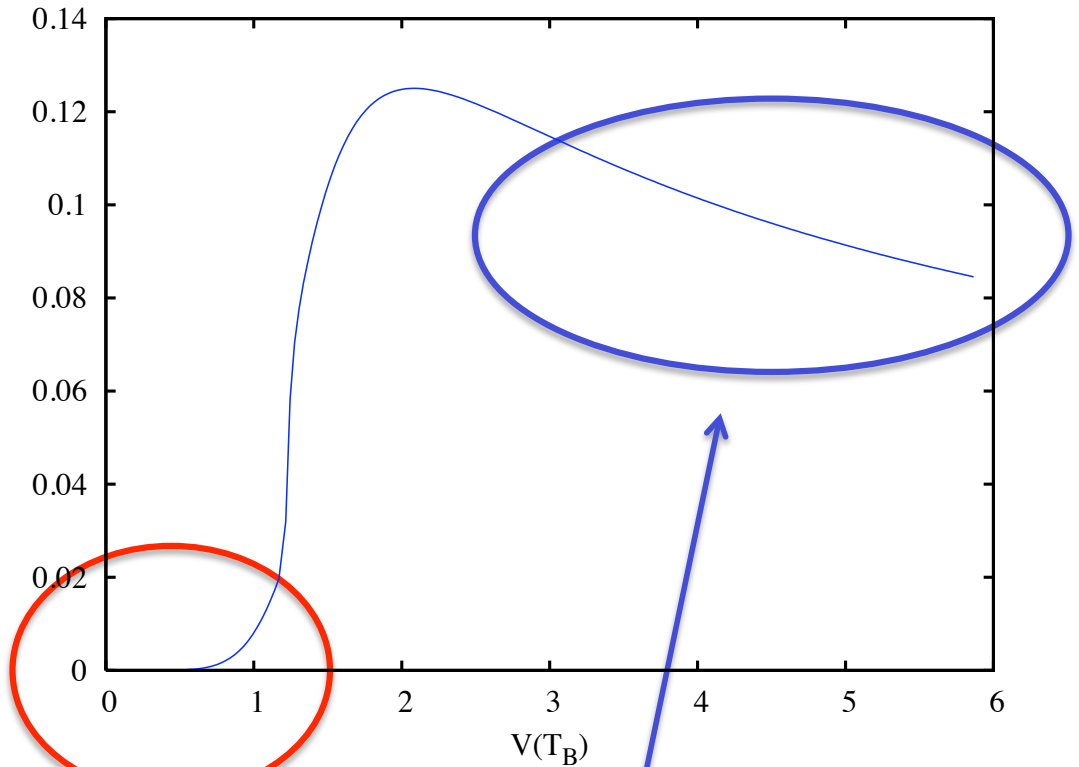
# I(V) curve (T=0)



- ✓ **Universal** curve:  $I/T_B = f(V/T_B)$
- ✓ Current enhancement for  $U > 0$  → **“Coulomb deblocking”**
- ✓ Large  $V$  decrease of the current → **effect of correlations of q.p.’s**

# DC noise (T=0)

$$S_{\omega=0} = \int dt \langle I(t)I(0) \rangle - \langle I^2 \rangle$$



$$S_{\omega=0} = 2e(G_0 V - I) (1 + \mathcal{O}(V^6)) = \mathcal{O}(V^7)$$

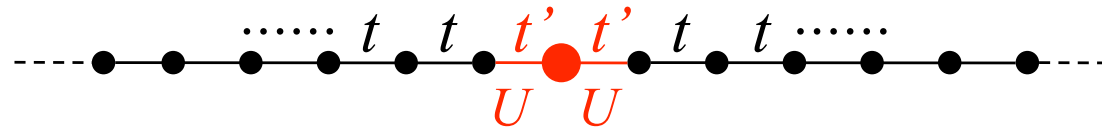
Back-scattered solitons

$$S_{\omega=0} = \frac{e}{2} I (1 + \mathcal{O}(V^{-3/2}))$$

Non-interacting electrons through double barrier

# Numerical approach

- Lattice model

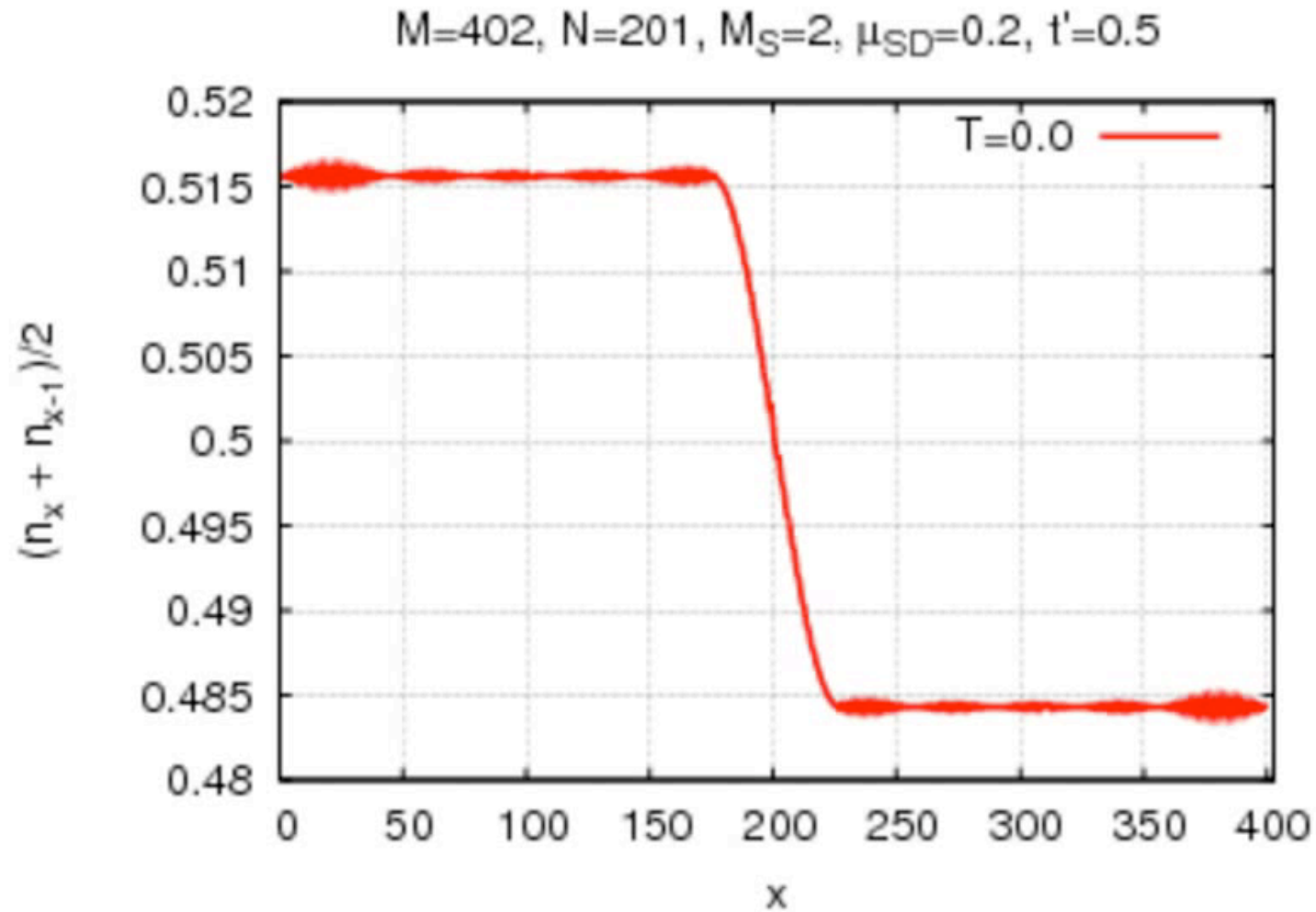


- Time-dependent DMRG

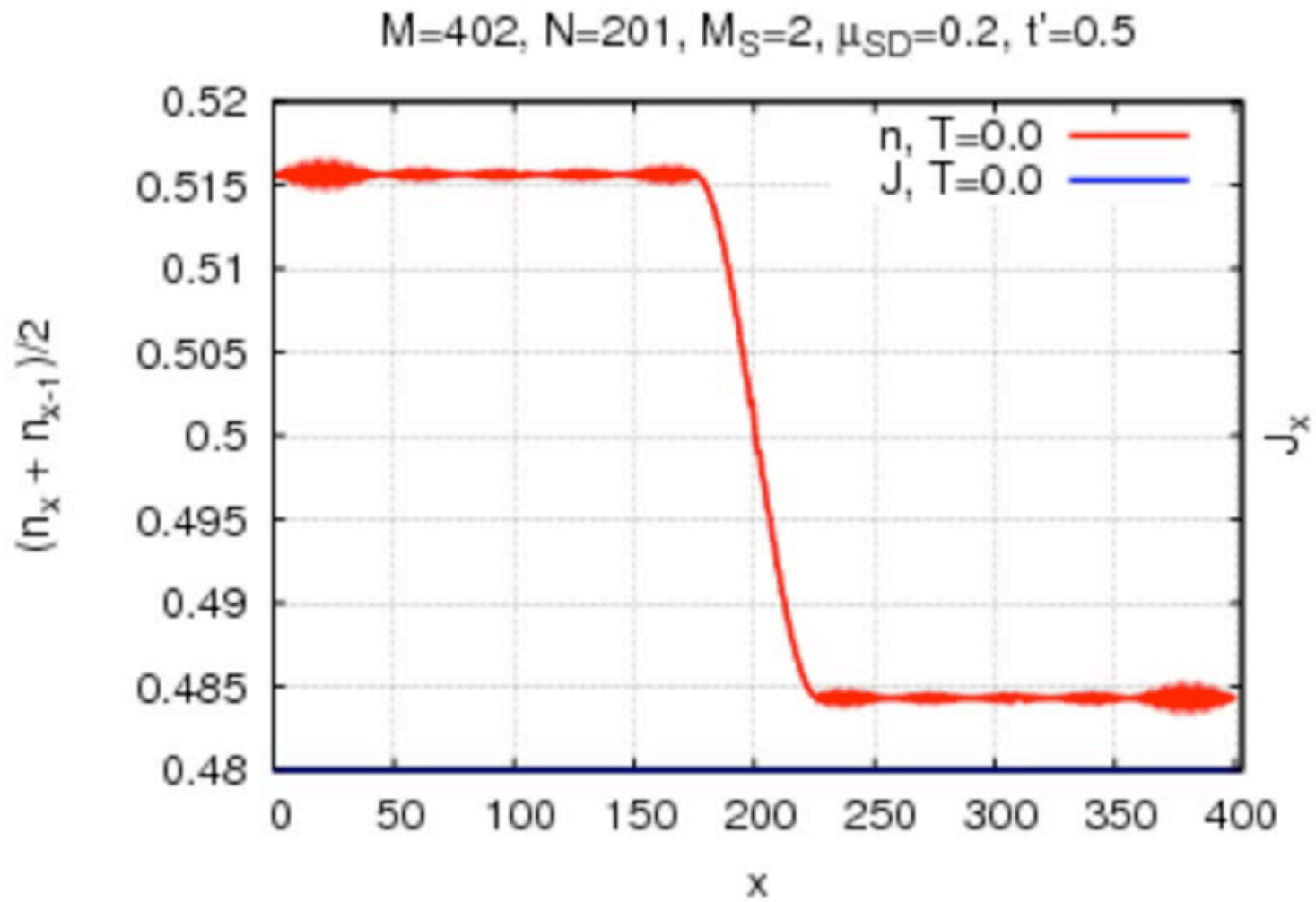
(S.White, A.Feiguin 2004, P.Schmitteckert 2004)

- Initial state ( $t < 0$ ): prepare the electrodes at different chemical potentials  $\pm V/2$
- Switch off the voltage at  $t = 0$
- Time-evolve using the full interacting Hamiltonian  $H_0 + H_I$   
(duration  $\Delta t < L_{\text{lead}} / v_F$ )
- Extrapolate to infinite size

# Electronic density



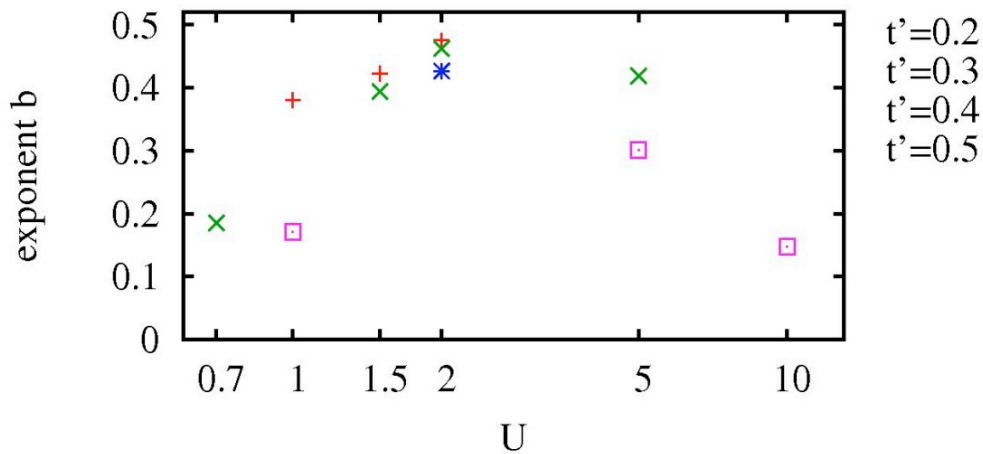
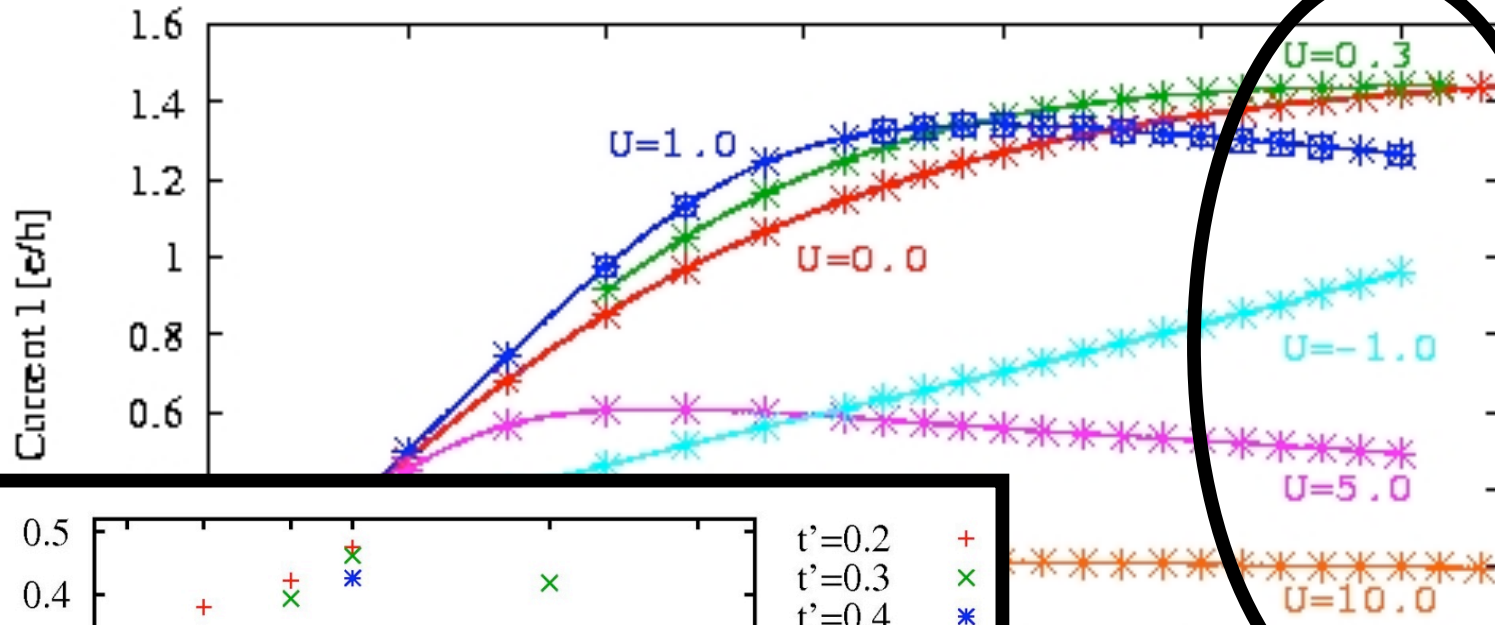
# Current





# $I(V)$ ( $T=0$ )

$M=96$  sites ;  $N=2000$  states kept ;  $t'=0.5$

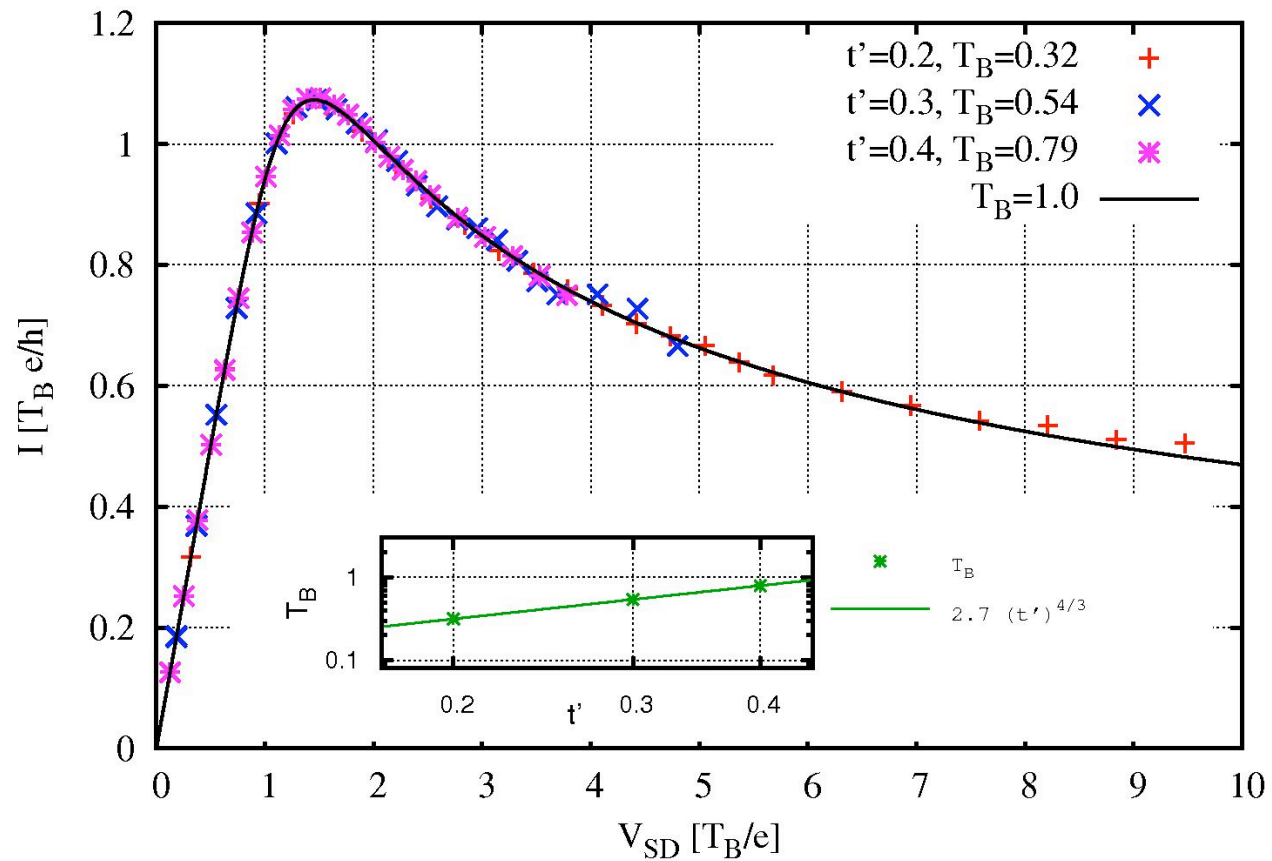


large  $V$  fit:

$$I \propto V^{-b}$$

# Self-dual point

Fitting parameter: hybridization temperature  $T_B$



$M=96$  sites ;  $N=2000$  states kept ;  $U=2$

# Noise - tdDMRG

- Need two-point function

$$S(t_1, t_2) = \langle \hat{I}(t_1) \hat{I}(t_2) \rangle - \langle \hat{I}(t_1) \rangle \langle \hat{I}(t_2) \rangle$$

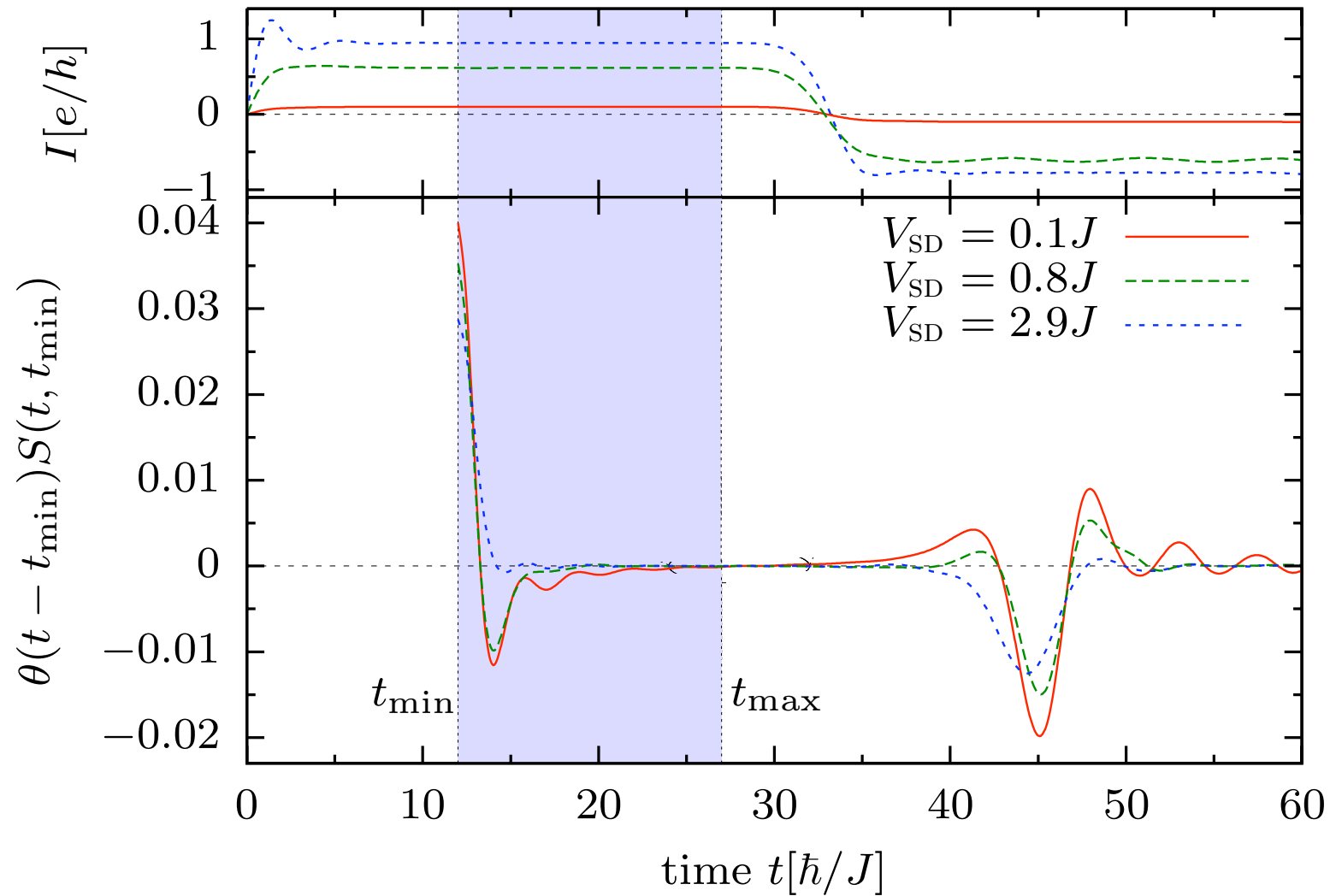
- **Quasi-stationary** state:

- No time translation invariance!
- Restriction on time-window:
  - Settling time  $t_S$  (transient regime, damped oscillation of the current)
  - Recurrence time  $t_R \propto L$  (finite size, wave packet bounces on the wall)



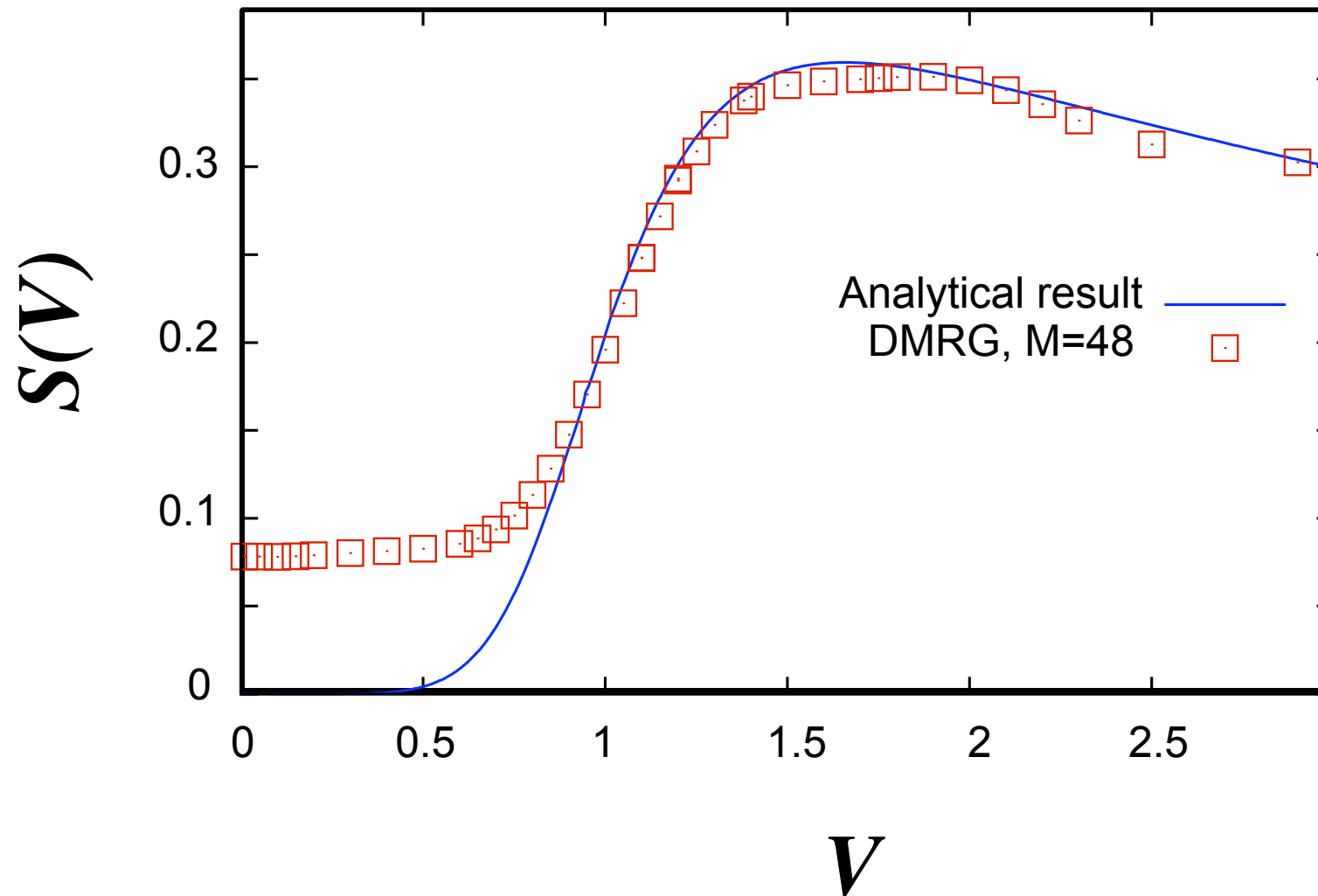
- Approximation of the noise: 
$$S_{num}(\omega) = 4 \operatorname{Re} \int_{t_{\min}}^{t_{\max}} dt e^{i\omega t} S(t_{\min}, t)$$
  - Neglects correlations outside window
  - need large sizes !

# Noise - tdDMRG

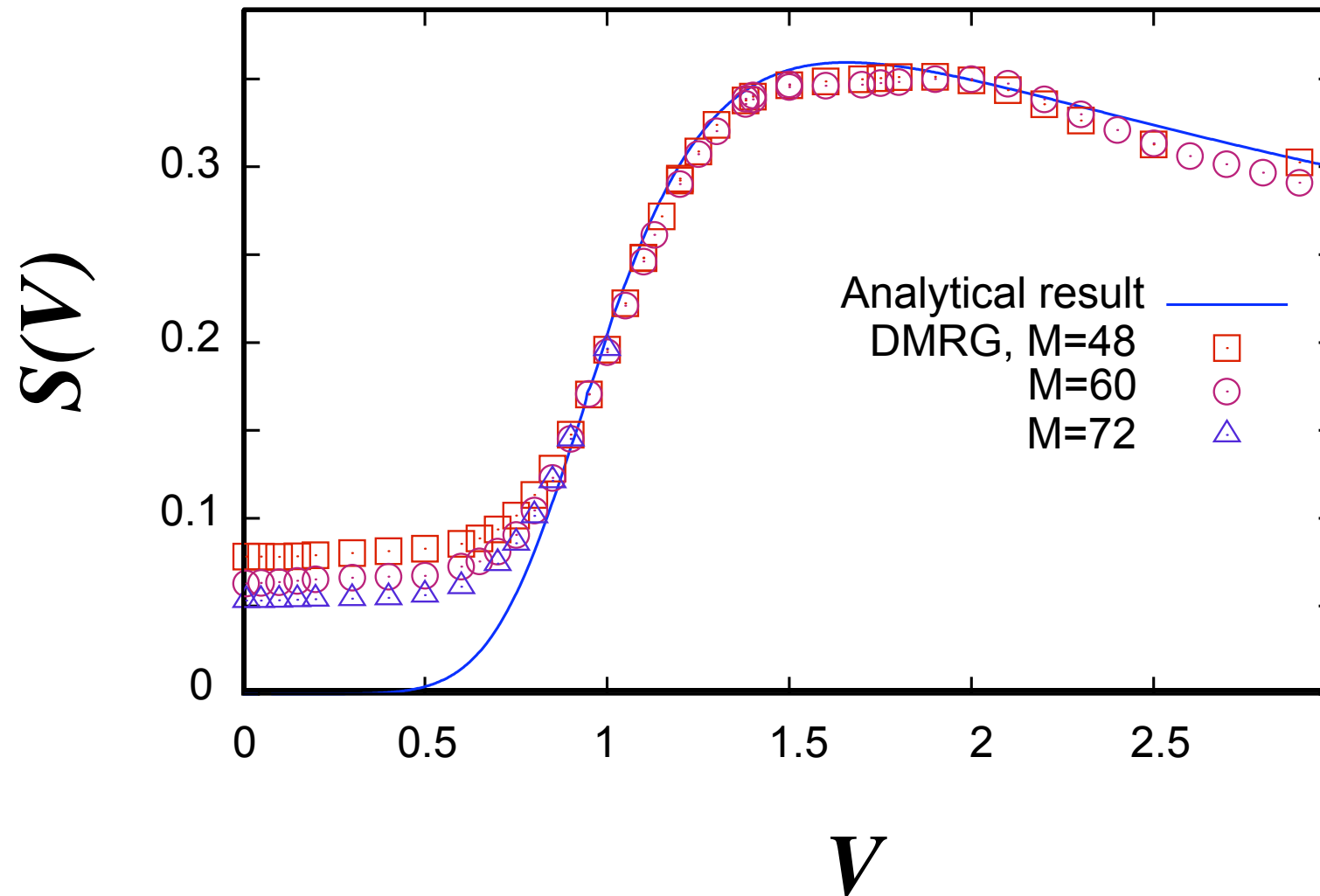


# Noise - tdDMRG

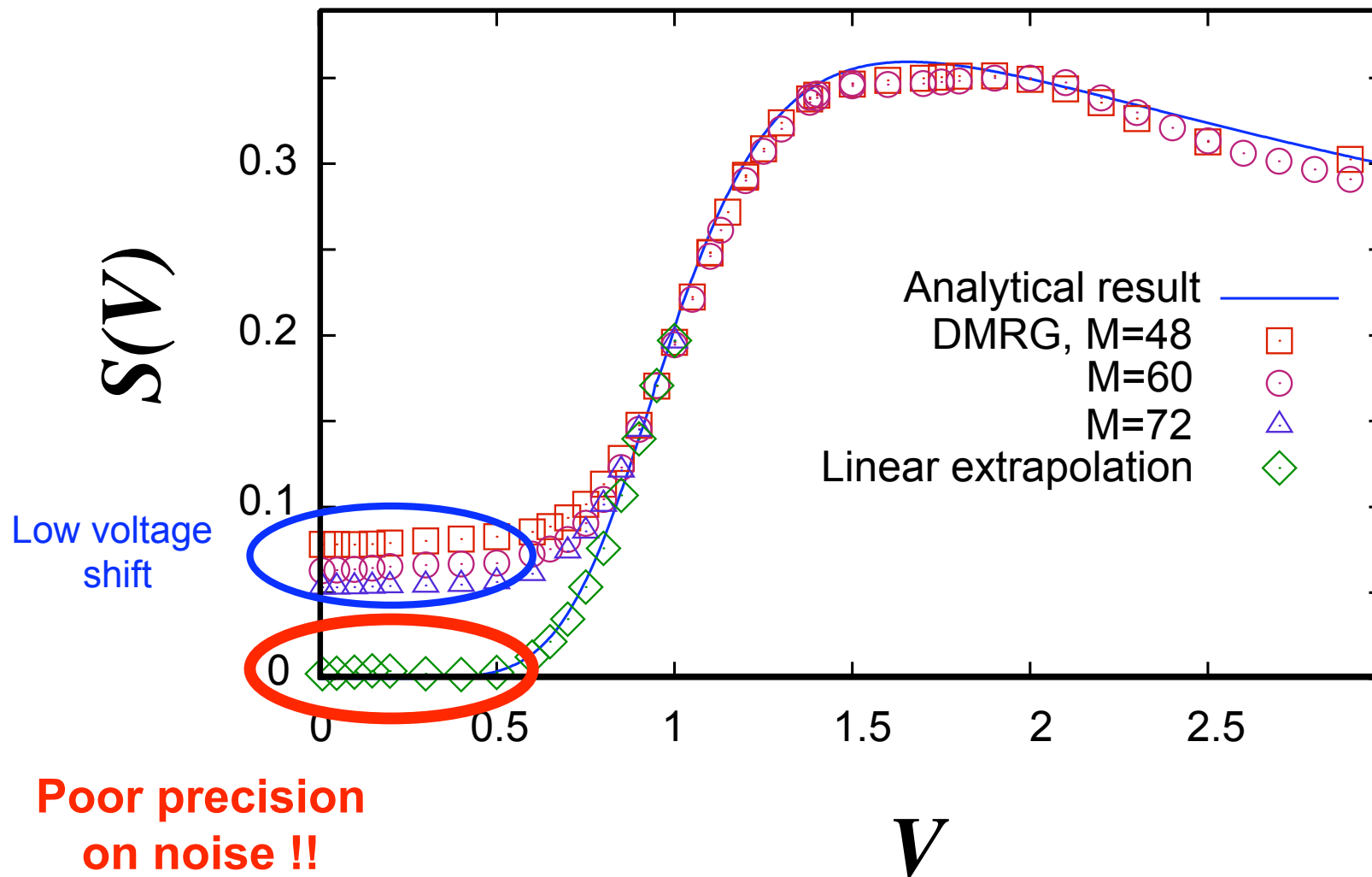
*No fitting parameter !*



# Noise - tdDMRG



# Noise - tdDMRG



# Low voltage

- At “zero” voltage, perfectly transparent structure:  $I(V) \xrightarrow{V \rightarrow 0} G_0 V$
- Analyse departure from perfect transparency by backscattering.

Backscattered current:

$$I_{BS} = G_0 V - I(V)$$

Backscattered Fano factor:

$$F_{BS}(V) = S(V) / I_{BS} \xrightarrow{V \rightarrow 0} e^*$$

- TBA approach predicts  $e^* = 2e$



# Low voltage shift

Low voltage shift of noise:

$$\lim_{\omega, V \rightarrow 0} S_{num}(\omega, V) \neq 0 \quad !!!$$

Finite size (recurrence time):

→ Finite lower frequency cut-off

$$\omega_{cut} \approx 1/t_R \approx 1/L$$

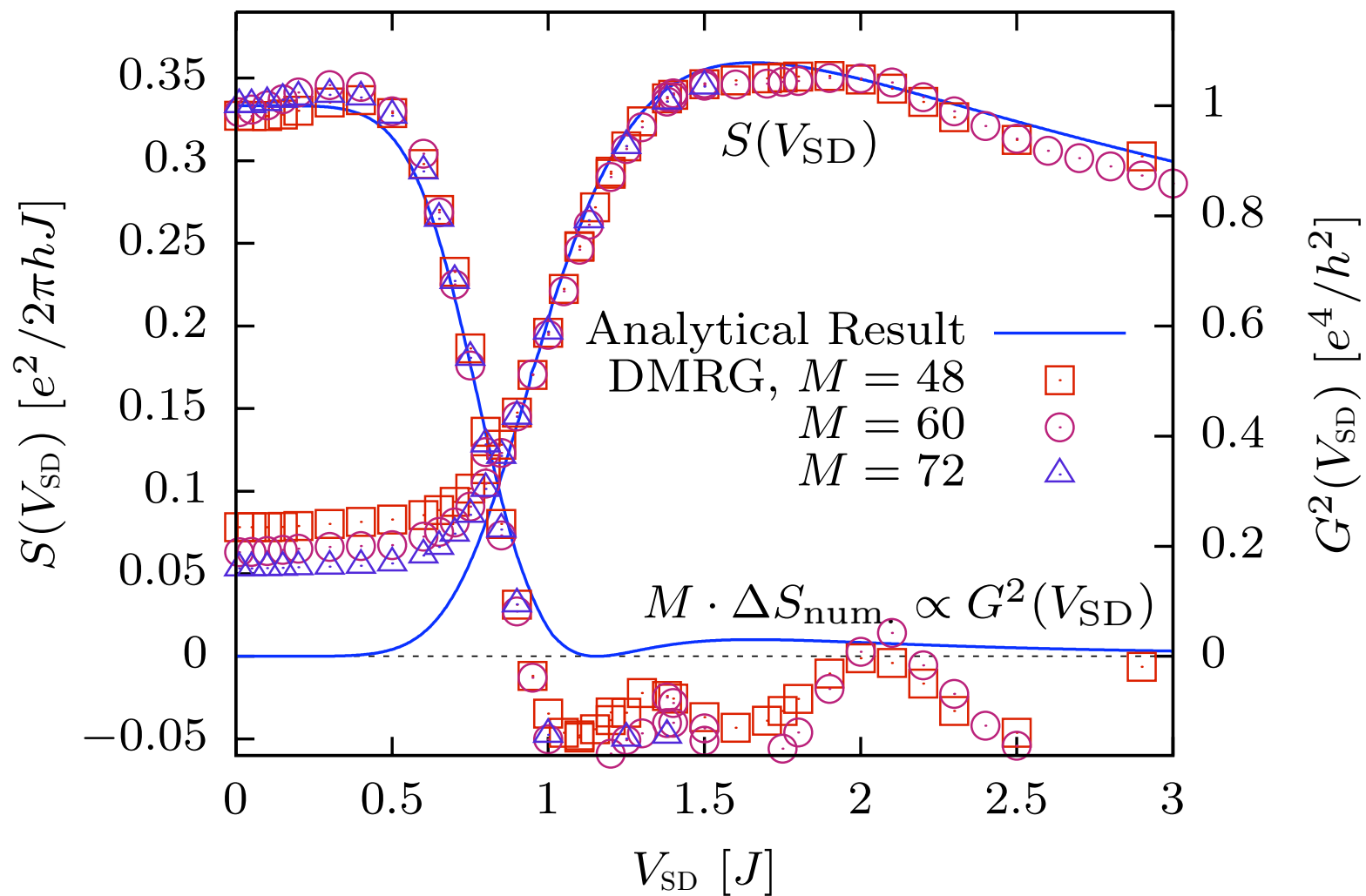
→ Finite correction of order 1/L

$$S_{num}(0, V) \approx S(\omega_{cut}, V) = S(0, V) + \omega_{cut} \partial_{\omega} S(0, V) + \dots$$

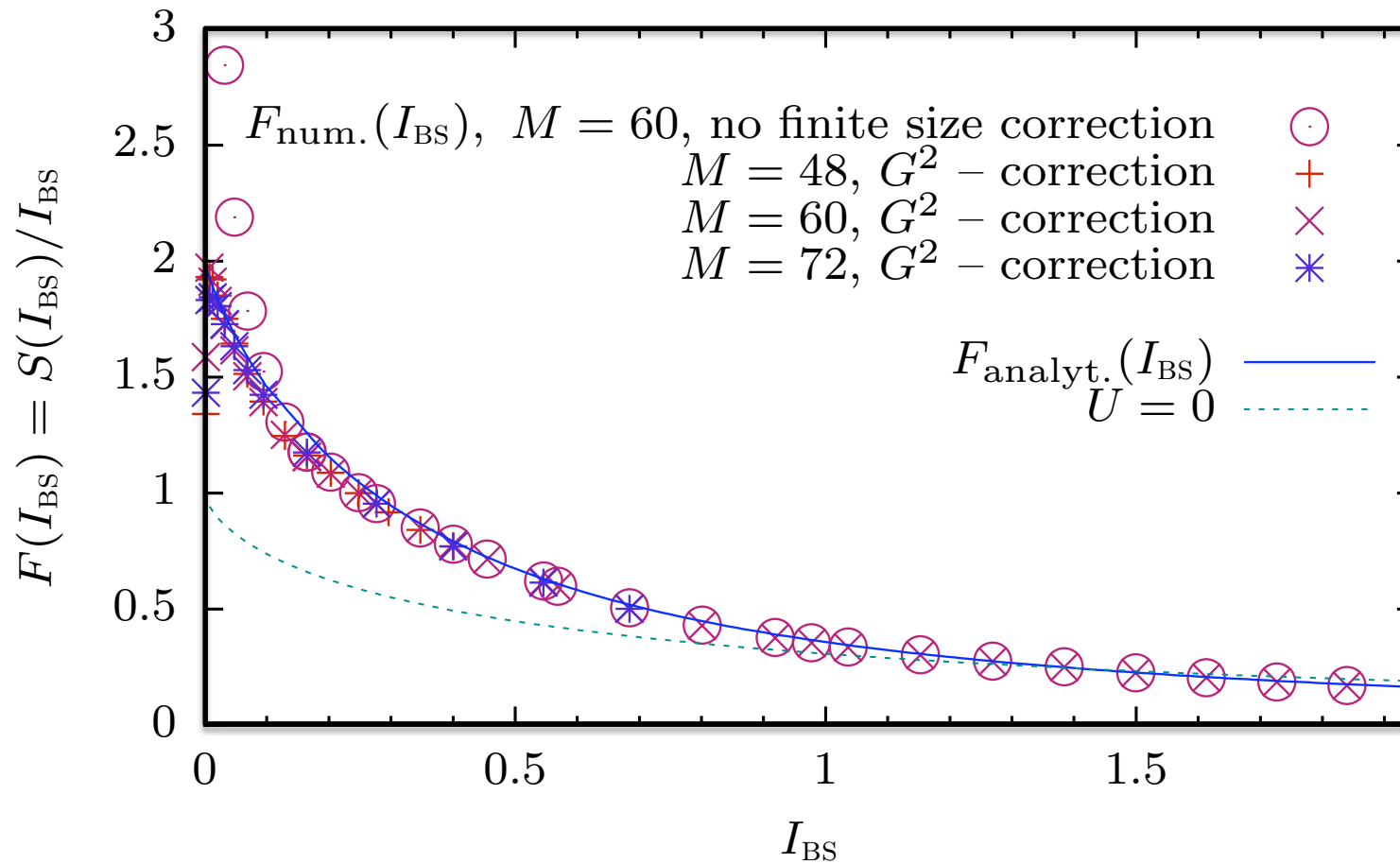
→ Use analytical estimate of correction (from free case):

$$\partial_{\omega} S(0, V) \propto G^2(V)$$

# 1/L correction



# Fano factor



# Conclusions

- Dressed TBA approach gives exact density matrix out-of-equilibrium
- Valid when *both* boundary scattering *and* Hershfield  $Y$  operator are diagonal (*sufficient* condition)
- td-DMRG gives current & noise, with remarkable accuracy

IRLM:

- Negative differential conductance
- Solitons have a clear signature in the low- $V$  noise